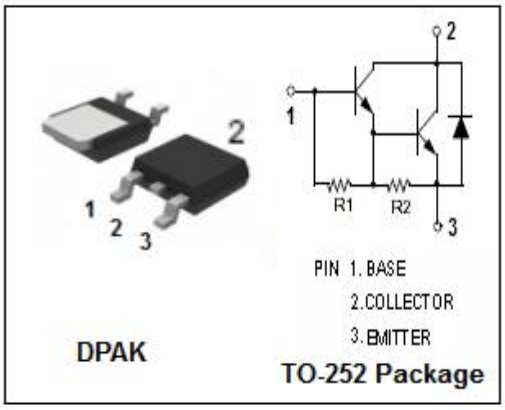
isc Silicon NPN Power Transistor NJD35N04T4G

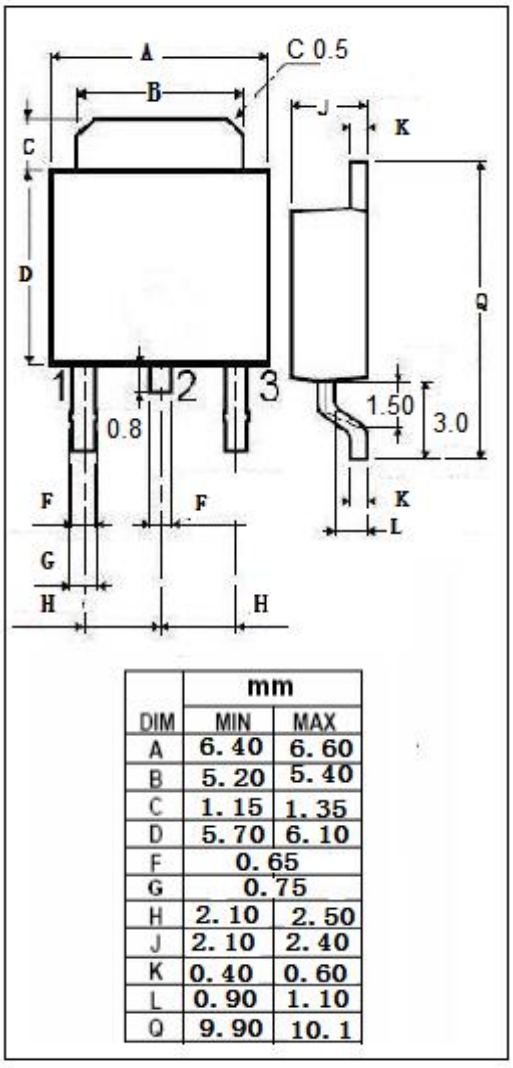
DESCRIPTION

- With TO-252(DPAK) packaging
- Reliable performance at higher powers
- Designed for inductive loads
- Fast switching speed
- Very low current requirements
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Internal combustion engine ignition control
- Switching regulators
- Motor controls
- Light ballast
- Photo flash



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Max.Collector Current-Continuous	8	A
I_B	Base Current-Continuous	0.5	A
P_D	Collector Power Dissipation @T_C=25℃	45	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=0.1mA; I_E=0	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C=10mA; I_B=0	350			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E=0.1mA;I_C=0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=2A; I_B=20mA			1.5	V
$V_{BE(sat)}$	Collector-Emitter Saturation Voltage	I_C=2A; I_B=20mA			2.0	V
$V_{BE(on)}$	Collector-Emitter On Voltage	I_C=2A;V_{CE}=2.0V			2.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 300V; I_B= 0			50	mA
I_{CES}	Collector Cutoff Current	V_{CB}= 500V;I_B= 0			50	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0			5	mA
h_{FE-1}	DC Current Cain	I_C= 2A ; V_{CE}= 2V	2000			
h_{FE-2}	DC Current Cain	I_C= 4A ; V_{CE}= 2V	300			